

General Description

The WSD80130DN56 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD80130DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

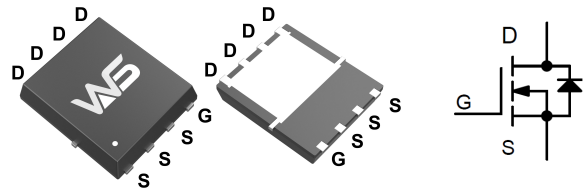
Product Summary

BV_{DSS}	R_{DSON}	I_D
80V	2.7mΩ	130A

Applications

- DC-DC converter switching for Networkong
- General purpose switching

DFN5X6-8 Pin Configuration



Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	80	V
V _{GS}	Gate-Source Voltage	±20	V
T _J	Maximum Junction Temperature	150	°C
I _D	Storage Temperature Range	-55 to 150	°C
I _D	Continuous Drain Current, V _{GS} =10V, T _C =25°C	130	A
	Continuous Drain Current, V _{GS} =10V, T _C =70°C	89	A
I _{DM}	Pulsed Drain Current, T _C =25°C	400	A
P _D	Maximum Power Dissipation, T _C =25°C	200	W
R _{θJC}	Thermal Resistance-Junction to Case	1.25	°C

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	80	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25 °C, I _D =1mA	---	0.043	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =40A	---	2.7	3.6	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-6.94	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =25 °C	---	---	2	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55 °C	---	---	10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Q _g	Total Gate Charge (10V)	V _{DS} =30V, V _{GS} =10V, I _D =30A	---	48.6	---	nC
Q _{gs}	Gate-Source Charge		---	17.5	---	
Q _{gd}	Gate-Drain Charge		---	10.4	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =2.5Ω, I _D =2A, R _L =15Ω.	---	20	---	ns
T _r	Rise Time		---	10	---	
T _{d(off)}	Turn-Off Delay Time		---	35	---	
T _f	Fall Time		---	12	---	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	4150	---	pF
C _{oss}	Output Capacitance		---	471	---	
C _{rss}	Reverse Transfer Capacitance		---	20	---	

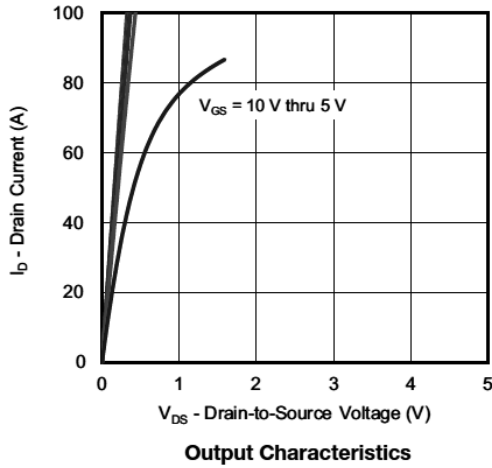
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	83.3	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25 °C	---	---	1.4	V

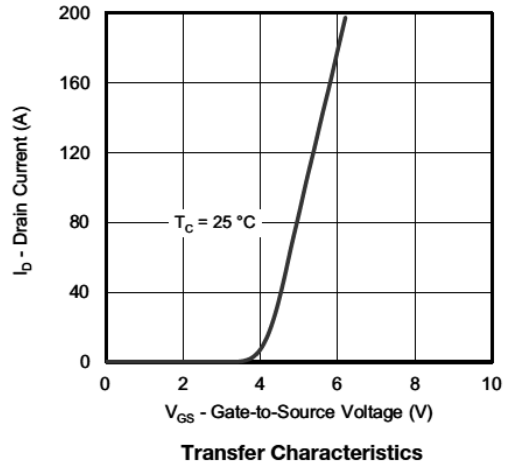
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition: T_J=25 °C, V_{DD}=40V, V_G=10V, L=0.5mH, R_G=25Ω

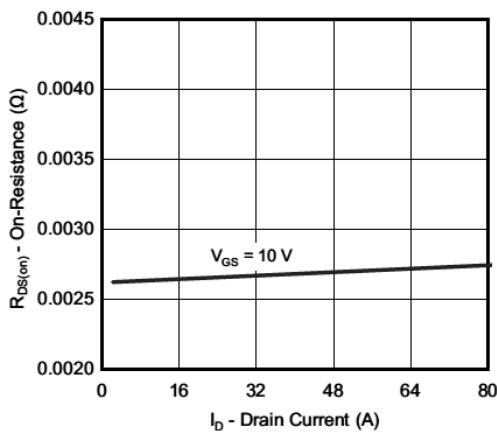
Typical Performance Characteristics ((T_J = 25 °C, unless otherwise noted))



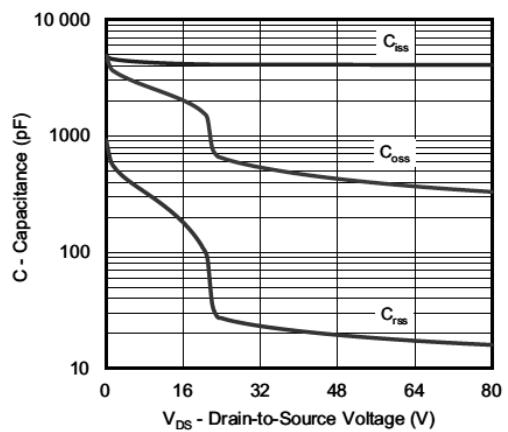
Output Characteristics



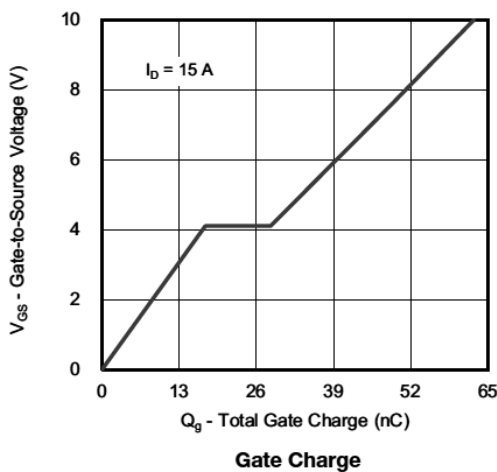
Transfer Characteristics



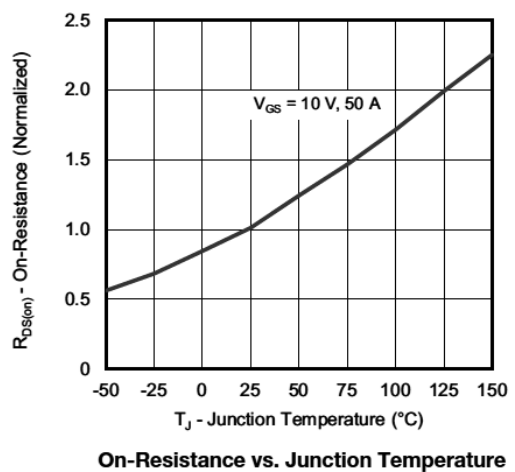
On-Resistance vs. Drain Current and Gate Voltage



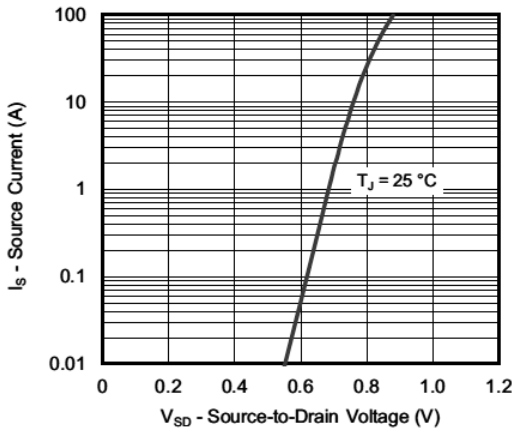
Capacitance



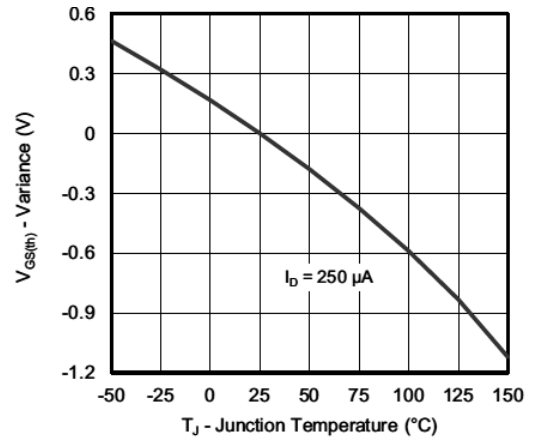
Gate Charge



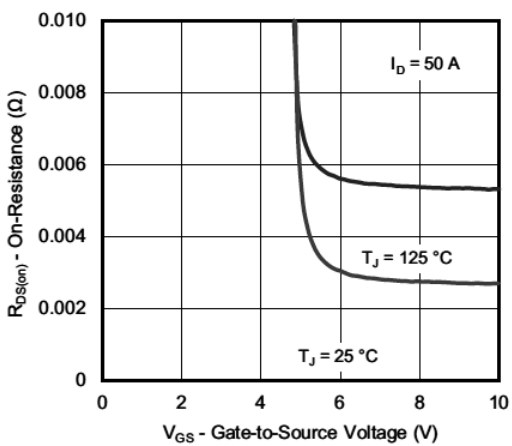
On-Resistance vs. Junction Temperature



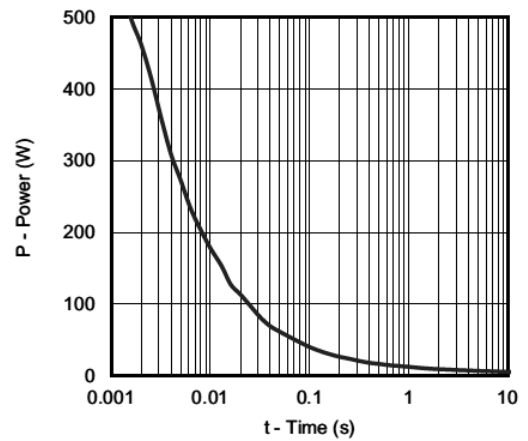
Source-Drain Diode Forward Voltage



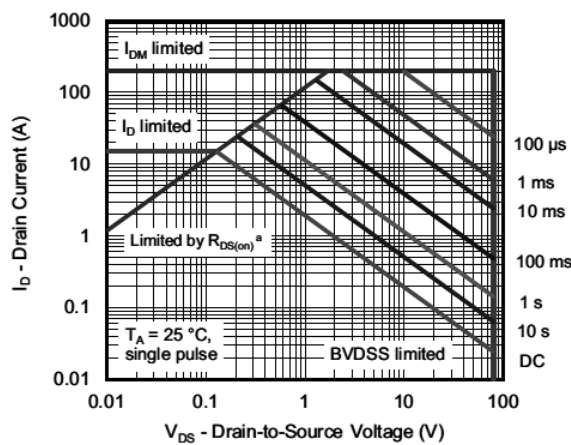
Threshold Voltage



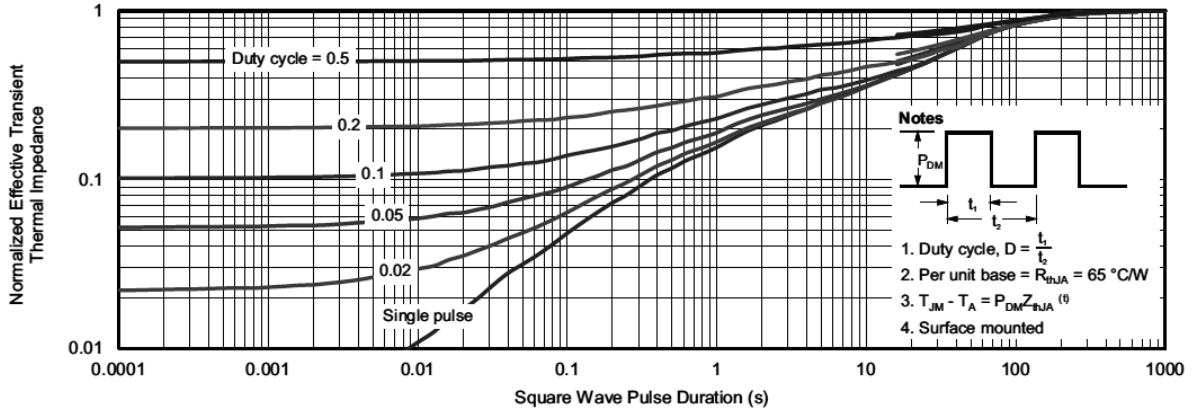
On-Resistance vs. Gate-to-Source Voltage



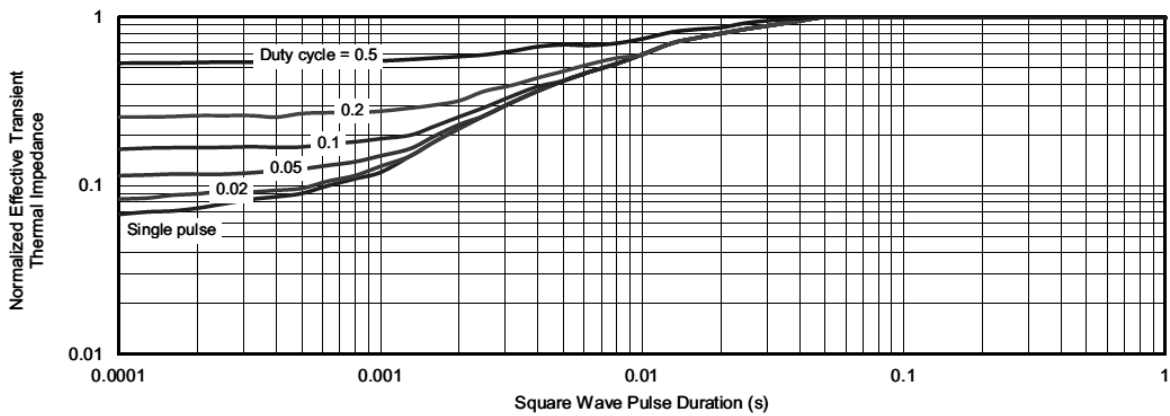
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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